

EDB101S THRU EDB106S

SINGLE-PHASE GLASS PASSIVATED SUPER FAST SURFACE MOUNT SILICON BRIDGE RECTIFIER



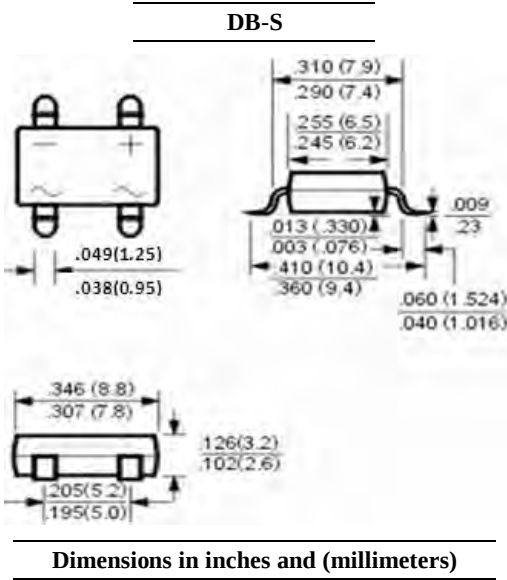
REVERSE VOLTAGE: 50 to 400 VOLTS
FORWARD CURRENT: 1.0 AMPERE

FEATURES

- Plastic material has Underwriters Laboratory Flammability Classification 94V-0
- High surge overload rating of 50 Amperes peak
- Ideal for printed circuit board
- Superfast recovery times for high efficiency
- Glass passivated chip junction

MECHANICAL DATA

Case: Molded plastic, DB-S
Epoxy: UL 94V-O rate flame retardant
Terminals: Leads solderable per MIL-STD-202, method 208 guaranteed
Mounting position: Any
Weight: 0.02ounce, 0.4gram



Maximum Ratings and Electrical Characteristics

Ratings at 25°C ambient temperature unless otherwise specified.
Single phase, half wave, 60Hz, resistive or inductive load.
For capacitive load, derate current by 20%.

	Symbols	EDB101S	EDB102S	EDB103S	EDB104S	EDB105S	EDB106S	Units
Maximum Recurrent Peak Reverse Voltage	V _{RRM}	50	100	150	200	300	400	Volts
Maximum RMS Voltage	V _{RMS}	35	70	105	140	210	280	Volts
Maximum DC Blocking Voltage	V _{DC}	50	100	150	200	300	400	Volts
Maximum Average Forward Rectified Current at T _A =40℃	I _(AV)	1.0						Amp
Peak Forward Surge Current, 8.3ms single half-sine-wave superimposed on rated load (JEDEC method)	I _{FSM}	50						Amp
Maximum Forward Voltage at 1.0A DC and 25℃	V _F	1.05				1.25		Volts
Maximum Reverse Current at T _A =25℃ at Rated DC Blocking Voltage T _A =125℃	I _R	5.0 1000						uAmp
Typical Junction Capacitance (Note 1)	C _J	15						pF
Maximum Reverse Recovery Time (Note 3)	T _{RR}	50						nS
Typical Thermal Resistance (Note 2)	R _{θJA}	38						℃/W
Typical Thermal Resistance (Note 2)	R _{θJL}	12						℃/W
Operating and Storage Temperature Range	T _J , T _{stg}	-55 to +150						℃

- NOTES:
- 1- Measured at 1 MHz and applied reverse voltage of 4.0 VDC.
 - 2- Thermal resistance from junction to ambient and from junction to lead mounted on P.C.B. with 0.5 x 0.5" (13 x 13mm) copper pads
 - 3- Reverse Recovery Test Conditions: $I_F=.5A$, $I_R=1A$, $I_{RR}=.25A$.

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康比電子
HORNBY ELECTRONIC

RATINGS AND CHARACTERISTIC CURVES

Fig. 1 - Derating Curve Output Rectified Current

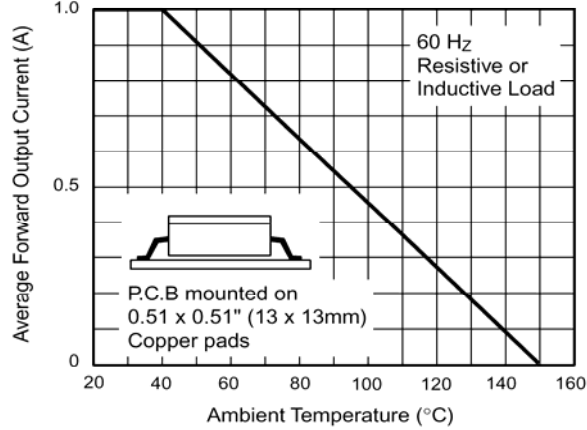


Fig. 2 - Maximum Non-Repetitive Peak Forward Surge Current

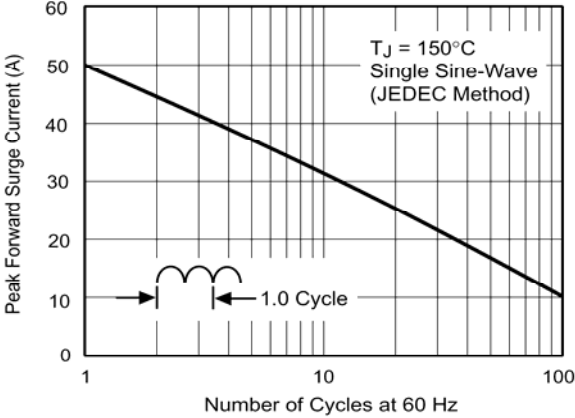


Fig. 3 - Typical Forward Characteristics Per Leg

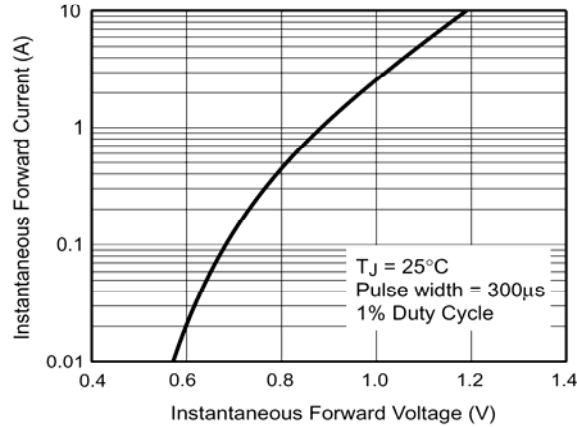


Fig. 4 - Typical Reverse Leakage Characteristics Per Leg

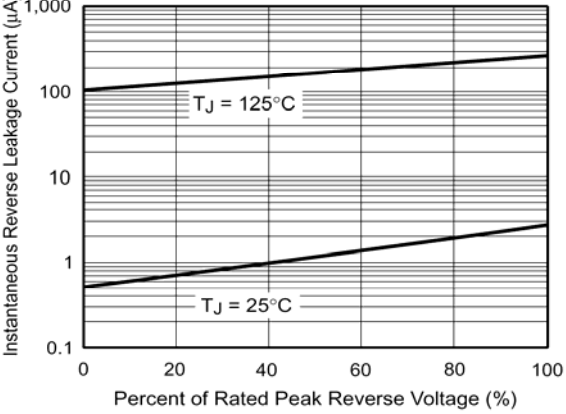


Fig. 5 - Typical Junction Capacitance Per Leg

